

Certificate of Analysis (CoA)

Mar. 12, 2026

Product Name: Manganese Telluride Sputtering Target, ST0325**Chemical Formula:** MnTe**Composition:** Mn : Te = 1 : 1 (atomic ratio)**Purity:** 99.9% (3N)**Dimensions:** Ø50.8 mm × 2.0 mm**Backing Plate:** Properly bonded to Copper backing plate, 3 mm thick**Quantity:** 1 pc**Lot Number:** CSJM-260312004**Manufactured by:** Thin-Film Materials

Physical Description

- Appearance: Dark gray dense target
 - Crystal Structure: Hexagonal (NiAs-type)
 - Fabrication: Powder metallurgy, sintered and bonded
 - Typical Density: ≥95% of theoretical
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Theoretical Stoichiometric Composition (Mass %)

(Atomic ratio: Mn : Te = 1 : 1)

Element	Symbol	Mass %
Manganese	Mn	~28.1%
Tellurium	Te	~71.9%

Balance: MnTe

Chemical Composition (by ICP-OES / XRF)

Element	Symbol	Specification
Manganese	Mn	1.0 (atomic ratio)

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Element	Symbol	Specification
Tellurium	Te	1.0 (atomic ratio)
Total Metallic Impurities	–	<1000 ppm
Individual Impurity (each)	–	<200 ppm

Bonding Information

- Bonding Method: Indium or elastomer bonding (standard sputtering bonding process)
 - Backing Plate Material: OFHC Copper
 - Backing Plate Thickness: 3 mm
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Handling & Storage

- Store in dry and clean environment.
 - Avoid mechanical shock to prevent cracking.
 - Handle with gloves to avoid surface contamination.
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Declaration

The material described above has been manufactured, inspected, and released in accordance with internal quality control procedures and complies with the specifications stated herein.

Authorized Signature:

Inspection Certificate by: Nancy LiuApprover by: Chen Qiang